

UF1000 THRU UF1008

ULTRAFAST SWITCHING RECTIFIER
VOLTAGE - 50 to 800 Volts
CURRENT - 10.0 Amperes

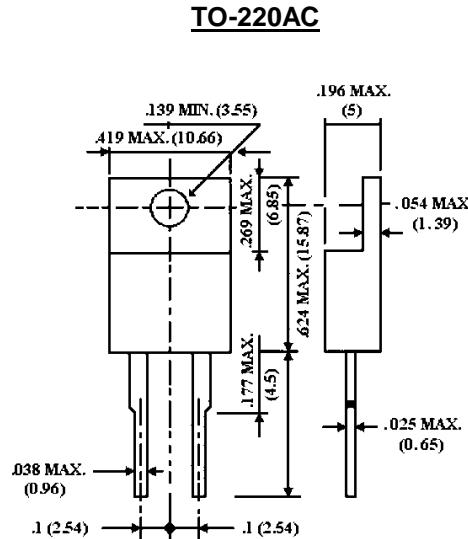


FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O Utilizing Flame Retardant Epoxy Molding Compound
- Exceeds environmental standards of MIL-S-19500/228
- Low power loss, high efficiency
- Low forward voltage, high current capability
- High surge capacity
- Ultra Fast recovery times, high voltage

MECHANICAL DATA

Case: TO-220AC molded plastic
 Terminals: Lead solderable per MIL-STD-202, Method 208
 Polarity: As marked
 Mounting Position: Any
 Weight: 0.08 ounce, 2.24 gram



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

TYPE NUMBER	UF1000	UF1001	UF1002	UF1003	UF1004	UF1006	UF1008	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	300	400	600	800	V
Maximum RMS Voltage	35	70	140	210	280	420	560	V
Maximum DC Blocking Voltage	50	100	200	300	400	600	800	V
Maximum Average Forward Rectified Current .375"(9.5mm) lead length @ T _A =100 °C					10.0			A
Peak Forward Surge Current, 8.3ms single half sine wave superimposed on rated load(JECEC method)					150			A
Maximum Instantaneous Forward Voltage at 10.0A	1.0		1.3		1.7			V
Maximum DC Reverse Current @ T _A =25 °C at Rated DC Blocking Voltage @ T _A =125 °C			10.0		500			uA uA
Maximum Reverse Recovery Time(Note 1)	50			100				ns
Typical Junction capacitance (Note 2)	80			50				pF
Typical Junction Resistance (Note 2) R _{JKJA}		15						°C/W
Operating and Storage Temperature Range T _J ,T _{STG}			-50 to +150					°C

NOTES:

1. Reverse Recovery Test Conditions: I_F=0.5A, I_R=1A, I_{rr}=0.25A
2. Measured at 1 MHz and applied reverse voltage of 4.0 VDC
3. Thermal resistance from junction to ambient and from junction to lead length 0.375"(9.5mm) P.C.B. mounted

RATING AND CHARACTERISTIC CURVES
UF1000 THRU UF1008

GM GarboMicro
Semiconductor

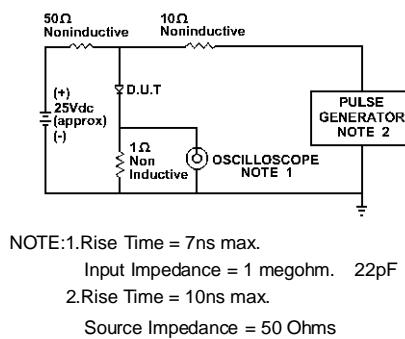


Fig. 1-REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

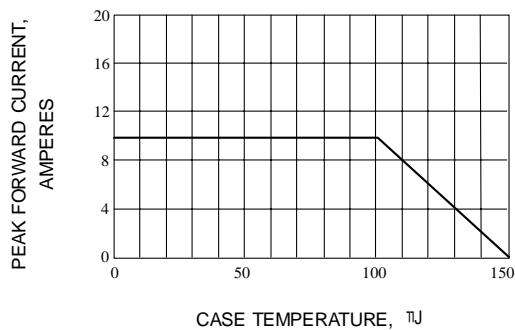


Fig. 1-TYPICAL FORWARD CURRENT DERATING CURVE

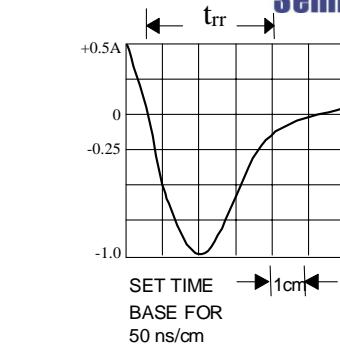


Fig. 2-TYPICAL REVERSE CHARACTERISTICS

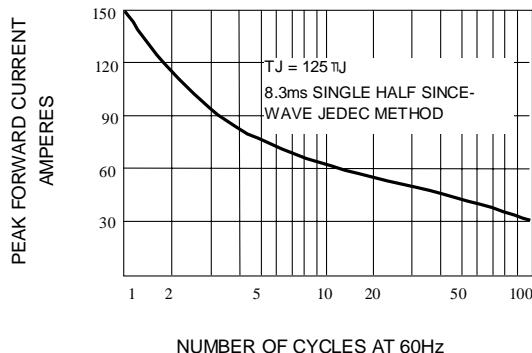


Fig. 3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

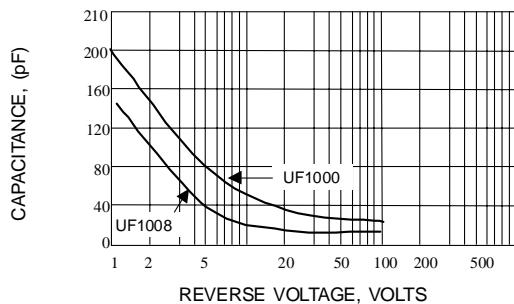


Fig. 4-TYPICAL JUNCTION CAPACITANCE

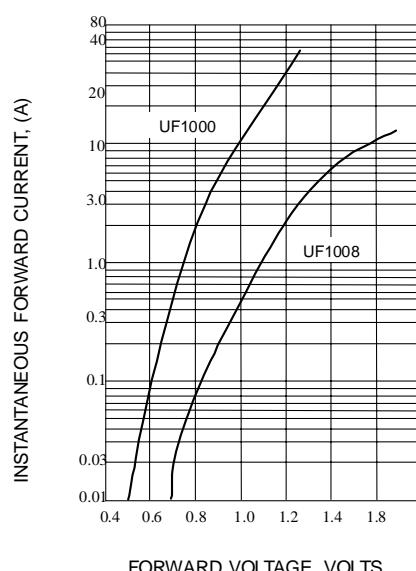


Fig. 5-TYPICAL FORWARD CHARACTERISTICS